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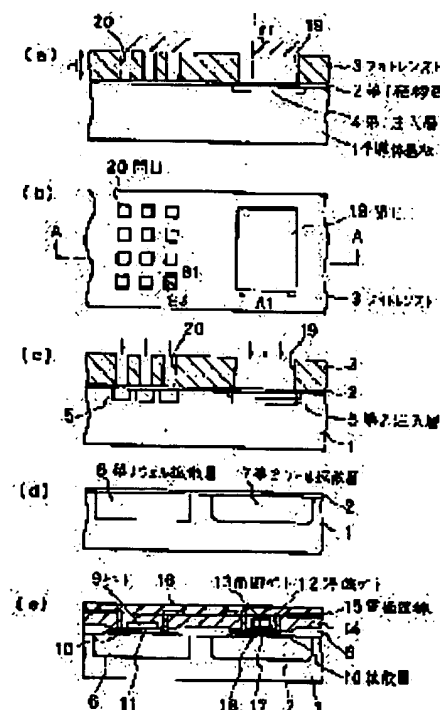
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## (54) MANUFACTURE OF SEMICONDUCTOR DEVICE

## (57)Abstract:

**PURPOSE:** To obtain the manufacture of a semiconductor device, in which mask processes are reduced when two kinds of different diffusion layers are formed.

**CONSTITUTION:** The manufacture of a semiconductor device includes a process in which a mask material 3 in required thickness is formed onto a semiconductor substrate 1, a process in which a plurality of first opening 20 having opening size smaller than the thickness of the mask material are formed in a region corresponding to a first ion implanting layer to the mask material 3 while a second opening 19 is shaped extending over approximately the whole region in a region corresponding to a second ion implanting layer, a process in which ions are implanted at an angle where the semiconductor substrate 1 is not exposed to the first openings 20, and a process in which ions are implanted at an angle where the semiconductor substrate 1 is exposed to the first openings 20.



## LEGAL STATUS

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